

N-Channel MOSFET

Description

The PNMIP500V2 is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in switching power supplies and adaptors.

MOSFET Product Summary				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
500	5.0 @ V _{GS} = 10V	2.0		



TO-251 (Top View)

Feature

- > Fast switching capability
- > Avalanche energy tested
- ➤ Improved dv/dt capability, high ruggedness

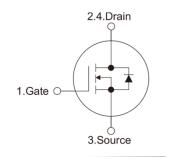
Mechanical data

> Case: TO-251

> Approx. Weight: 0.315g (0.011oz)

➤ Lead free finish, RoHS compliant

Case Material: "Green" molding compound, UL flammability classification 94V-0, "Halogen-free".



Schematic diagram

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Drain-Source Voltage	V _{DS}	500	V
Gate-Source Voltage	V_{GS}	±30	V
Drain Current-Continuous $ \frac{T_{C}=25^{\circ}C}{T_{C}=100^{\circ}C} $	· I _D	2.0 1.3	А
Pulsed Drain Current ²⁾	I _{DM}	8.0	А
Avalanche Energy, Single Pulsed ³⁾	E _{AS}	35	mJ
Peak Diode Recovery dv/dt ⁴⁾	dv/dt	2.1	V/ns
Maximum Power Dissipation	P_{D}	54	W
Operating Junction and Storage Temperature Range	T_J, T_STG	-55 ~ +150	°C
Junction-to-Ambient	$R_{ heta JA}$	63	°C/W
Junction to Case	$R_{ heta JC}$	2.31	°C/W

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	$V_{GS} = 0V, I_{D} = 250 \mu A$	500	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 500V,V _{GS} = 0V	-	-	1.0	μΑ	
Gate-Body Leakage Current	I _{GSS}	$V_{GS} = \pm 30 \text{V}, V_{DS} = 0 \text{V}$	-	-	±100	nA	
On Characteristics							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0	-	4.0	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10V,I _D = 1.0A	-	5.0	7.0	Ω	
Dynamic Characteristics							
Input Capacitance	C _{lss}		-	156	-		
Output Capacitance	C _{oss}	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	-	24	-	pF	
Reverse Transfer Capacitance	C _{rss}		-	2.2	-		
Switching Characteristics							
Turn-on Delay Time ⁵⁾	t _{d(on)}		-	8.4	-	ns	
Turn-on Rise Time	t _r	V _{DS} = 250V, V _{GS} = 10V,	-	22.4	-		
Turn-Off Delay Time	$t_{d(off)}$	$I_D = 2.0A, R_G = 25\Omega^{5,6}$	-	15.1	-		
Turn-Off Fall Time	t _f		-	24.1	-		
Total Gate Charge ⁵⁾	Q_g		-	8.97	-		
Gate-Source Charge	Q_{gs}	$V_{DS} = 400V, V_{GS} = 10V,$ $I_{D} = 2.0A, I_{G} = 1mA^{5,6}$	-	2.51	-	nC	
Gate-Drain Charge	Q_{gd}		-	4.02	-		
Drain-Source Diode Characteristic	Drain-Source Diode Characteristics						
Diode Forward Voltage ⁵⁾	V _{SD}	$V_{GS} = 0V, I_{S} = 2.0A$	-	-	1.4	V	
Diode Continuous Current	I _S		-	-	2.0	Α	
Diode Pulsed Current	I _{SM}		-	-	8.0	Α	
Reverse Recovery Time ⁵⁾	t _{rr}	$V_{GS} = 0V, I_{S} = 2.0A,$	-	309	-	nS	
Reverse Recovery Charge	Q_{rr}	di/dt = 100A/μs	-	0.95	-	μC	

^{1.}Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

^{2.} Repetitive Rating: Pulse width limited by maximum junction temperature. 3. L = 30mH, I_{AS} = 2.6A, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25°C 4. I_{SD} ≤ 2A, di/dt ≤ 200A/ μ s, V_{DD} ≤ BV $_{DSS}$, Starting T_{J} = 25°C 5. Pulse Test: Pulse width ≤ 300 μ s, Duty cycle ≤ 2%.

^{6.} Essentially independent of operating temperature.

Typical Characteristics

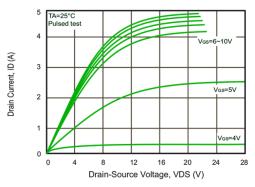


Fig.1 Drain Current vs. Gate-Source Voltage

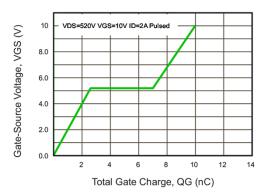


Fig.3 Gate Charge Characteristics

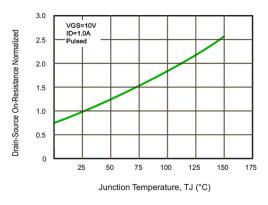


Fig.5 Drain-Source On-Resistance vs. Junction Temperature

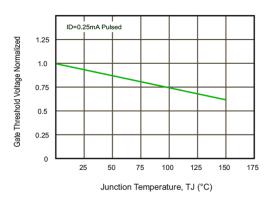


Fig.7 Gate Threshold Voltage vs. Junction Temperature

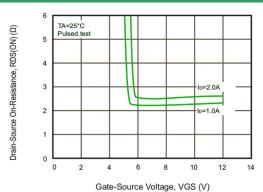


Fig.2 Drain-Source On-Resistance vs. Gate-Source Voltage

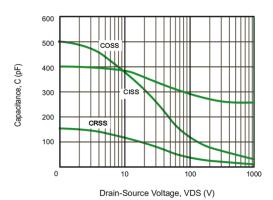


Fig.4 Capacitance Characteristics

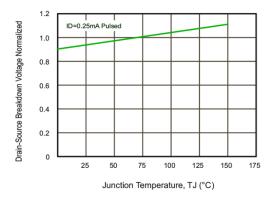


Fig.6 Breakdown Voltage vs. Junction Temperature

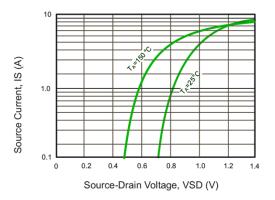


Fig.8 Source Current vs. Source-Drain Voltage

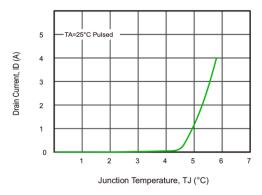


Fig.9 Drain Current vs. Gate-Source Voltage

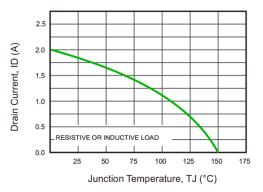


Fig.11 Drain Current vs. Junction Temperature

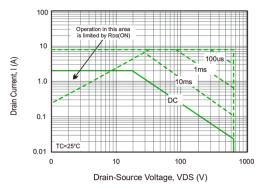


Fig.13 Safe Operating Area

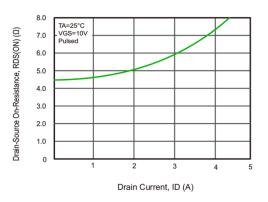
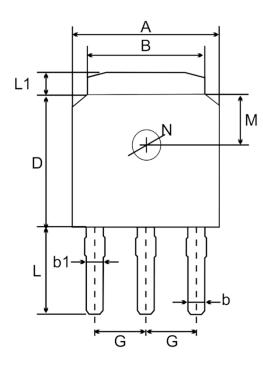


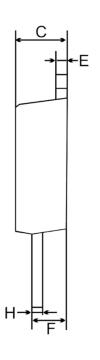
Fig.10 Drain-Source On-Resistance vs. Drain Current

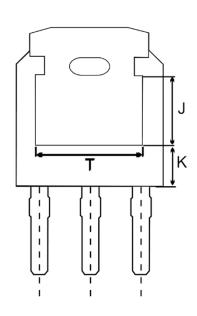


Fig.12 Power Dissipation vs. Junction Temperature

Product dimension (TO-251)







Dim	Millimeters		Inches		
Dim	Min	Max	Min	Max	
А	6.30	6.70	0.248	0.264	
В	5.10	5.50	0.201	0.217	
b	0.30	0.80	0.012	0.031	
b1	0.76	0.90	0.030	0.035	
С	2.10	2.50	0.083	0.098	
D	5.90	6.30	0.232	0.248	
Е	0.40	0.60	0.016	0.024	
F	1.30	1.80	0.051	0.071	
G	2.29 Typ.		0.090 Typ.		
Н	0.45	0.55	0.018	0.022	
L	3.90	4.30	0.154	0.169	
L1	0.80	1.20	0.031	0.047	
М	1.80 Typ.		0.071 Typ.		
N	1.30 Typ.		0.051 Typ.		
J	3.16 Ref.		0.124 Ref.		
К	1.80 Ref.		0.071 Ref.		
Т	4.83 Ref.		0.190 Ref.		

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